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ABSTRACT OF THE DISCLOSURE

A gate electrode of an n-channel IGFET includes a first region composed of at least a first IV group element and a second IV group element which are different from each other, and a second region composed of the first IV group element. Similarly, a gate electrode of a p-channel IGFET includes first and second regions. For example, the first region is made of SiGe while the second region is made of Si. In both of the n-channel and P-channel IGFET, silicide electrodes are formed on the gate electrodes 4N and 4P through silicidation of at least parts of the second regions.

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